



EXPRESS MAIL LABEL NO. EV674901312US

PATENTS

Attorney Docket No.: ELM-2 DIV. 6

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Glenn J. Leedy
Application No. : 10/614,067 Confirmation No.: 8117
Filed : July 3, 2003
For : THREE DIMENSIONAL STRUCTURE INTEGRATED
CIRCUIT
Group Art Unit : 2822
Examiner : Pamela E. Perkins

Mail Stop RCE
Commissioner for Patents
P.O. Box 1450
Alexandria, Virginia 22313-1450

INFORMATION DISCLOSURE STATEMENT

Sir:

In accordance with 37 C.F.R. §§ 1.56 and 1.97,
applicant wishes to call the attention of the Examiner to the
following documents:

U.S. Patent Documents

US 3,636,358	01/18/1972	Groschwitz	(6)
US 3,932,932	01/20/1976	Goodman	(2)
US 4,028,547	06/07/1977	Eisenberger	(3)
US 4,393,127	07/12/1983	Greschner et al.	(3)
US 4,528,072	07/09/1985	Kurosawa et al.	(2)
US 4,566,037	01/21/1986	Takatsu et al.	(6)
US 4,604,162	08/05/1986	Sobczak	
US 4,622,632	11/11/1986	Tanimoto et al.	(6)
US 4,810,889	03/07/1989	Yokomatsu et al.	(3)
US 4,849,857	07/18/1989	Butt et al.	
US 4,928,058	05/22/1990	Williamson	
US 4,990,462	02/05/1991	Sliwa	
US 5,051,326	09/24/1991	Celler et al.	(3)
US 5,110,712	05/05/1992	Kessler et al.	
US 5,119,164	06/02/1992	Sliwa et al.	

U.S. Patent Documents

US 5,166,962	11/24/1992	Murooka et al.	(3)
US 5,169,805	12/08/1992	Mok et al.	(4)
US 5,188,706	02/23/1993	Hori et al.	(3)
US 5,245,277	09/14/1993	Furtek et al.	(6)
US 5,283,107	02/01/1994	Bayer et al.	(6)
US 5,284,804	02/08/1994	Moslehi	
US 5,293,457	03/08/1994	Arima et al.	(6)
US 5,399,505	03/21/1995	Dasse et al.	(6)
US 5,432,999	07/18/1995	Capps et al.	(5)
US 5,450,603	09/12/1995	Davies	(6)
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US 5,572,689	11/05/1996	Gallup et al.	(6)
US 5,577,050	11/19/1996	Bair et al.	(1)
US 5,615,163	03/25/1997	Sakui et al.	
US 5,745,673	04/28/1998	Di Zenzo et al.	(1)
US 5,786,629	07/28/1998	Faris	
US 5,818,748	10/06/1998	Bertin et al.	(1)
US 6,092,174	07/18/2000	Roussakov	(6)
US 6,154,809	11/28/2000	Ikenaga et al.	(6)
US 6,301,653	10/09/2001	Mohamed et al.	(6)
US 6,300,935	10/09/2001	Sobel et al.	(6)
US 6,320,593	11/20/2001	Sobel et al.	(6)
US 2005-00223656	02/03/2005	Leedy	(6)
US 6,355,976	03/12/2002	Faris	
US 6,894,392	05/17/2005	Gudesen et al.	(6)

Foreign Patent Documents

EP 0 201 380	12/17/1986	Fairchild Semiconductor Corp.
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EP 0 526 551	02/10/1993	The Commonwealth of Australia
EP 0 554 063	08/04/1993	Canon Kabushiki Kaisha
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Svechnikov, S.V.; Kobyl'yatskaya, M.F.; Kimarskii, V.I.; Kaufman, A.P.; Kuzovlev, Yu. I.; Cherepov, Ye. I.; Fomin, B.I.; "A switching plate with aluminum membrane crossings of conductors"; 1972

Sun, R.C.; Tisone, T.C.; Cruzan, P.D.; "Internal stresses and resistivity of low-voltage sputtered tungsten films (microelectronic cct. conductor)"; March 1973; pp. 1009-16

Wade, T.E.; "Low temperature double-exposed polyimide/oxide dielectric for VLSI multilevel metal interconnection"; 1982; pp. 516-19

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Salazar, M.; Wilkins, C.W., Jr.; Ryan, V.W.; Wang, T.T.; "Low stress films of cyclized polybutadiene dielectrics by vacuum annealing"; Oct. 21-22, 1986; pp. 96-102

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a spin-applied dielectric for use in multilevel
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using microfabricated structures"; 1988; pp.
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- Reche, J.J. H.; "Control of thin film materials
properties used in high density multichip
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- Maw, T.; Hopla, R.E.; "Properties of a
photoimageable thin polyimide film"; Nov. 26-
29-, 1990; pp. 71-6
- Guckel, H.; "Surface micromachined pressure
transducers"; 1991; pp. 133-146
- Draper, B. L.; Hill, T.A.; "Stress and stress
relaxation in integrated circuit metals and
dielectrics"; July-Aug. 1991; pp. 1956-62

Nonpatent Literature Documents

Garino, T.J.; Harrington, H. M.; "Residual stress in PZT thin films and its effect on ferroelectric properties"; 1992; pp. 341-7

The aforementioned references are listed on the accompanying Form PTO/SB/08 (submitted in duplicate). Pursuant to 37 C.F.R. 1.98 (a)(2), applicant is not submitting copies of the aforementioned U.S. patent document references. Copies of the aforementioned Foreign Patent Documents and Non-Patent Literature Documents are enclosed herewith.

Applicant reserves the right to establish the patentability of the claimed invention over any of the information provided herewith, and/or to prove that this information may not be prior art, and/or to prove that this information may not be enabling for the teachings purportedly offered.

The aforementioned U.S. Patent Documents identified by (1) were cited in an Office Action mailed on October 18, 2005 in co-pending commonly assigned U.S. Patent Application No. 10/143,200. Documents identified by (2) were cited in an Office Action mailed on November 17, 2005 in co-pending commonly assigned U.S. Patent Application No. 10/742,057. Documents identified by (3) were cited in an Office Action mailed on December 7, 2005 in co-pending commonly assigned U.S. Patent Application No. 10/766,557. The Document identified by (4) was cited in an Office Action mailed on December 13, 2005 in co-pending commonly assigned U.S. Patent Application No. 10/742,282. The document identified by (5) was cited in an Office Action mailed on December 19, 2005 in co-pending commonly assigned U.S. Patent Application No. 10/379,820. The U.S. Patent Documents and

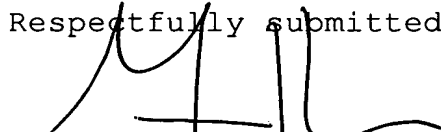
Nonpatent Literature Documents identified by (6) were cited in an Office Action mailed on January 26, 2006 in co-pending commonly assigned U.S. Patent Application No. 10/741,647.

It is respectfully requested that these references be: (1) fully considered by the Patent and Trademark Office during the examination of this application; and (2) printed on any patent which may issue on this application. Applicant requests that a copy of Form PTO-SB/08, as considered and initialed by the Examiner, be returned with the next communication.

This Statement is submitted concurrently with a request for continued examination under 37 C.F.R. §1.114. Pursuant to 37 C.F.R. §1.97(b)(4), applicant believes no fee is due in connection with this statement. However, if for any reason a fee is due, the Director is hereby authorized to charge payment of any fees required in connection with this Statement, or to credit any overpayment of the same, to Deposit Account No. 06-1075 (Order No.: 001202-0132). A duplicate copy of this Statement is enclosed herewith.

An early and favorable action is respectfully requested.

Respectfully submitted,



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PTO/SB/08a/b (08-03)

Approved for use through 07/31/2006. OMB 0651-0031

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Substitute for form 1449A/B/PTO			Complete if Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)			Application Number	10/614,067 (Conf. No. 8117)
			Filing Date	July 3, 2003
			First Named Inventor	Leedy
			Art Unit	2822
			Examiner Name	Pamela Perkins
Sheet 1 of 3			Attorney Docket Number	ELM-2 Div. 6

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)			
		US 3,636,358	01/18/1972	Groschwitz	
		US 3,932,932	01/20/1976	Goodman	
		US 4,028,547	06/07/1977	Eisenberger	
		US 4,393,127	07/12/1983	Greschner et al.	
		US 4,528,072	07/09/1985	Kurosawa et al.	
		US 4,566,037	01/21/1986	Takatsu et al.	
		US 4,604,162	08/05/1986	Sobczak	
		US 4,622,632	11/11/1986	Tanimoto et al.	
		US 4,810,889	03/07/1989	Yokomatsu et al.	
		US 4,849,857	07/18/1989	Butt et al.	
		US 4,928,058	05/22/1990	Williamson	
		US 4,990,462	02/05/1991	Sliwa	
		US 5,051,326	09/24/1991	Celler et al.	
		US 5,110,712	05/05/1992	Kessler et al.	
		US 5,119,164	06/02/1992	Sliwa et al.	
		US 5,166,962	11/24/1992	Murooka et al.	
		US 5,169,805	12/08/1992	Mok et al.	
		US 5,188,706	02/23/1993	Hori et al.	
		US 5,245,277	09/14/1993	Furtek et al.	
		US 5,283,107	02/01/1994	Bayer et al.	
		US 5,284,804	02/08/1994	Moslehi	
		US 5,293,457	03/08/1994	Arima et al.	
		US 5,399,505	03/21/1995	Dasse et al.	
		US 5,432,999	07/18/1995	Capps et al.	
		US 5,450,603	09/12/1995	Davies	
		US 5,470,693	11/28/1995	Sachdev et al.	
		US 5,517,457	05/14/1996	Sakui et al.	
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		US 5,577,050	11/19/1996	Bair et al.	
		US 5,615,163	03/25/1997	Sakui et al.	
		US 5,745,673	04/28/1998	Di Zenzo et al.	
		US 5,786,629	07/28/1998	Faris	
		US 5,818,748	10/06/1998	Bertin et al.	
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		US 6,300,935	10/09/2001	Sobel et al.	
		US 6,320,593	11/20/2001	Sobel et al.	
		US 2005-00223656	02/03/2005	Leedy	
		US 6,355,976	03/12/2002	Faris	
		US 6,894,392	05/17/2005	Gudesen et al.	

Examiner Signature		Date Considered	
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Sheet	2	of	3	Attorney Docket Number	ELM-2 Div. 6

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		Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)	MM-DD-YYYY			
		EP 0 201 380	12/17/1986	Fairchild Semiconductor Corp.		
		EP 0 224 418	06/03/1987	Fujitsu Limited		
		EP 0 419 898	04/03/1991	Siemens Aktiengesellschaft		
		EP 0 455 455	11/06/1991	AT&T Corp.		
		EP 0 487 302	05/27/1992	Shin-Etsu Handotai Company Ltd.		
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		WO 89/ 10255	11/02/1989	3D Systems, Inc.		
		WO 90/ 09093	08/23/1990	Polythetics, Inc.		
		WO 92/ 17901	10/15/1992	Integrated System Assemblies Corp.		

NON PATENT LITERATURE DOCUMENTS				
Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²	
		Jones, R.E., Jr. "An evaluation of methods for passivating silicon integrated circuits", April 1972; pp. 23-8		
		Svechnikov, S.V.; Kobylatskaya, M.F.; Kimarskii, V.I.; Kaufman, A.P.; Kuzovlev, Yu. I.; Cherepov, Ye. I.; Fomin, B.I.; "A switching plate with aluminum membrane crossings of conductors"; 1972		
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		Chen, Y.S.; Fatemi, H.; "Stress measurements on multilevel thin film dielectric layers used in Si integrated circuits"; May-June 1986; pp. 645-9		
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		Wolf, Stanley and Richard N. Tauber; Silicon Procesing For the VLSI Era, Volume 1: Process Technology; Sunset Beach, CA: Lattice Press, 1986, pages 191-194		

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Sheet	3	of	3	Attorney Docket Number	ELM-2 Div. 6

NON PATENT LITERATURE DOCUMENTS				
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		Pai, Pei-Lin; "Multilevel Interconnection Technologies--A Framework And Examples"; 1987; pp. 1871		
		Pei-lin Pai; Chetty, A.; Roat, R.; Cox, N.; Chiu Ting; "Material characteristics of spin-on glasses for interlayer dielectric applications"; November 1987, pp. 2829-34		
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		Garino, T.J.; Harrington, H. M.; "Residual stress in PZT thin films and its effect on ferroelectric properties"; 1992; pp. 341-7		

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. ¹ Applicant's unique citation designation number (optional). ² See Kinds Codes of USPTO Patent Documents at www.uspto.gov or MPEP 901.04. ³ Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴ For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵ Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST.16 if possible. ⁶ Applicant is to place a check mark here if English language Translation is attached.

Examiner Signature		Date Considered	
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